

## 1. Supplementary information

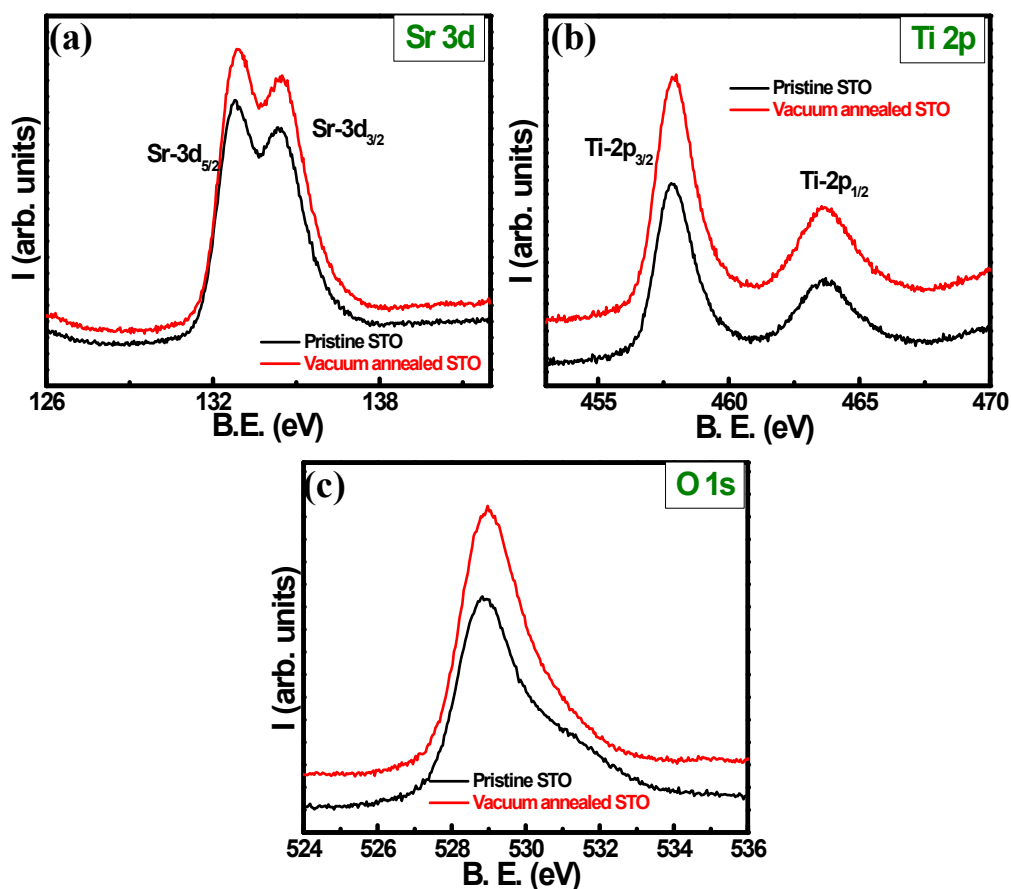
### Interface mediated semiconducting to metallic like transition in ultrathin $\text{Bi}_2\text{Se}_3$ films on (100) $\text{SrTiO}_3$ grown by molecular beam epitaxy

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**Figure S1:** XPS spectra for pristine and vacuum annealed  $\text{SrTiO}_3$  single crystal substrate.

High resolution XPS spectra of (a) Sr 3d (b)Ti 2p and (c)O 1s.

